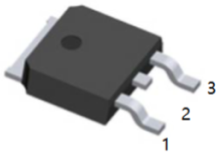
UMW®

FDD86113

100V N-Channel MOSFET

General Description

This N-Channel logic Level MOSFETs are produced using advanced process that incorporates Shielded Gate technology. This process has been optimized for the onsta-te resistance and yet maintain superior switching performance.



1.G 2.D 3.S

TO-252(DPAK) top view

Features

- Shielded Gate MOSFET Technology
- V_{DS}=100V
- I_D (at V_{GS}=10V)4.2A
- $R_{DS(ON)}$ (at V_{GS}=10V) < 104mΩ
- $R_{DS(ON)}$ (at V_{GS} = 4.5V) < 156mΩ
- HBM ESD protection level > 6 kV typical (Note 4)
- High performance trench technology for extremely low $R_{DS(on)}$
- High power and current handling capability in a widely used surface mount package

Application

- DC-DC conversion

MOSFET Maximum Ratings T_C= 25 °C unless otherwise noted

Symbol	Parameter			Ratings	Units
V_{DS}	Drain to Source Voltage			100	V
V_{GS}	Gate to Source Voltage			±20	V
I_D	Drain Current -Continuous	T_C = 25 °C		5.5	A
	-Continuous	T_A = 25 °C	(Note 1a)	4.2	
	-Pulsed			15	
E_{AS}	Single Pulse Avalanche Energy		(Note 3)	12	mJ
P_D	Power Dissipation	T_C = 25 °C		29	W
	Power Dissipation	T_A = 25 °C	(Note 1a)	3.1	
T_J, T_{STG}	Operating and Storage Junction Temperature Range			-55 to +150	°C

Thermal Characteristics

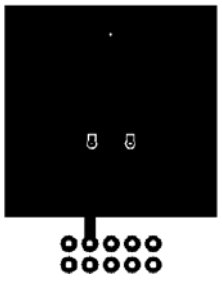
$R_{\theta JC}$	Thermal Resistance, Junction to Case	(Note 1)	4.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	96	

Electrical Characteristics T_J = 25 °C unless otherwise noted

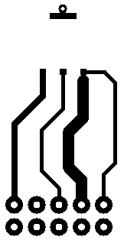
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		72		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 80 V, V_{GS} = 0 V			1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0 V			±10	μA
On Characteristics						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	1	1.6	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		-5		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 4.2 A		80	100	mΩ
		V_{GS} = 4.5 V, I_D = 3.4 A		110	140	
g_{FS}	Forward Transconductance	V_{DS} = 5 V, I_D = 4.2 A		9		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 50 V, V_{GS} = 0 V, f = 1MHz		213	285	pF
C_{oss}	Output Capacitance			55	75	pF
C_{rss}	Reverse Transfer Capacitance			2.4	5	pF
R_g	Gate Resistance			1.4		Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 50 V, I_D = 4.2 A, V_{GS} = 10 V, R_{GEN} = 6 Ω		3.6	10	ns
t_r	Rise Time			1.3	10	ns
$t_{d(off)}$	Turn-Off Delay Time			9.7	20	ns
t_f	Fall Time			1.6	10	ns
$Q_{g(TOT)}$	Total Gate Charge	V_{GS} = 0 V to 10 V; V_{DD} = 50 V, I_D = 4.2 A		3.7	6	nC
$Q_{g(TOT)}$	Total Gate Charge	V_{GS} = 0 V to 4.5 V; V_{DD} = 50 V, I_D = 4.2 A		1.9	3	
Q_{gs}	Gate to Source Charge	V_{DD} = 50 V, I_D = 4.2 A		0.6		nC
Q_{gd}	Gate to Drain “Miller” Charge	V_{DD} = 50 V, I_D = 4.2 A		0.7		nC
Drain-Source Diode Characteristics						
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 4.2 A (Note 2)		0.88	1.3	V
		V_{GS} = 0 V, I_S = 1.7 A (Note 2)		0.80	1.2	
t_{rr}	Reverse Recovery Time	I_F = 4.2 A, di/dt = 100 A/μs		31	49	ns
Q_{rr}	Reverse Recovery Charge			20	33	nC

NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 40 °C/W when mounted on a 1 in^2 pad of 2 oz copper



b) 96 °C/W when mounted on a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0 %.
3. Starting T_J = 25 °C, L = 1 mH, I_{AS} = 5 A, V_{DD} = 90 V, V_{GS} = 10 V.
4. The diode connected between gate and source serves only as protection against ESD. No gate overvoltage rating is implied.

Typical Characteristics T_J = 25 °C unless otherwise noted

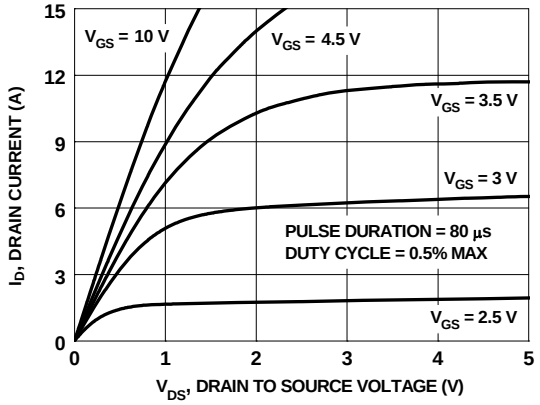


Figure 1. On-Region Characteristics

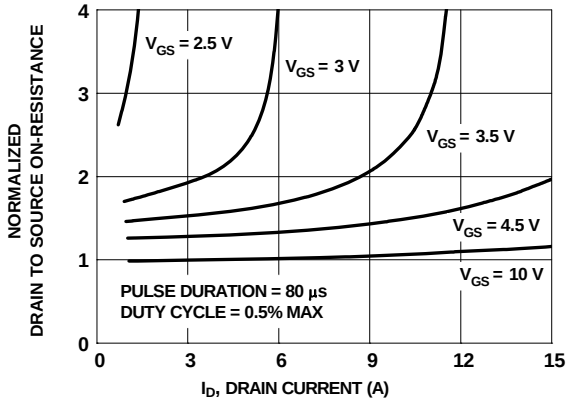


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

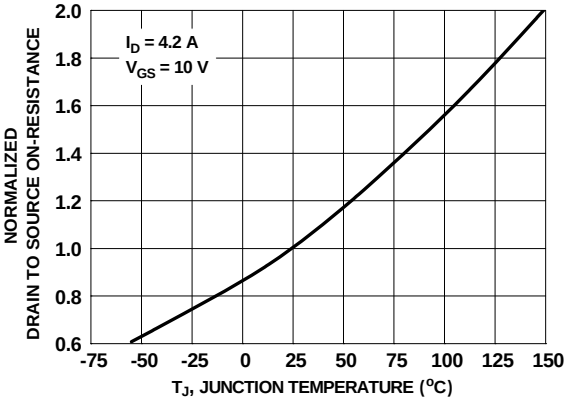


Figure 3. Normalized On-Resistance vs Junction Temperature

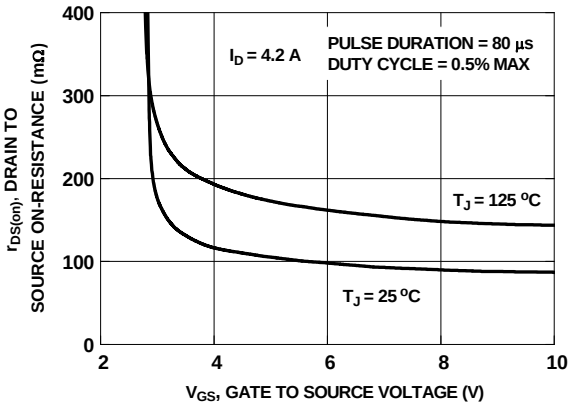


Figure 4. On-Resistance vs Gate to Source Voltage

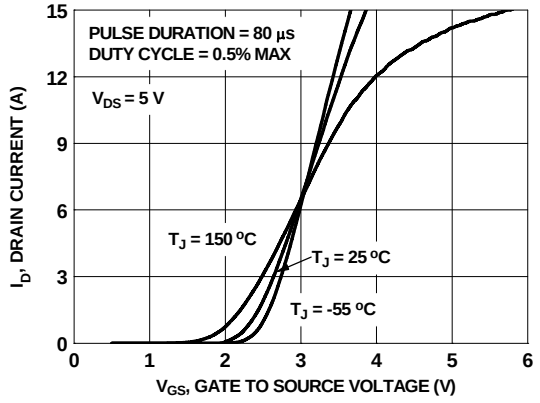


Figure 5. Transfer Characteristics

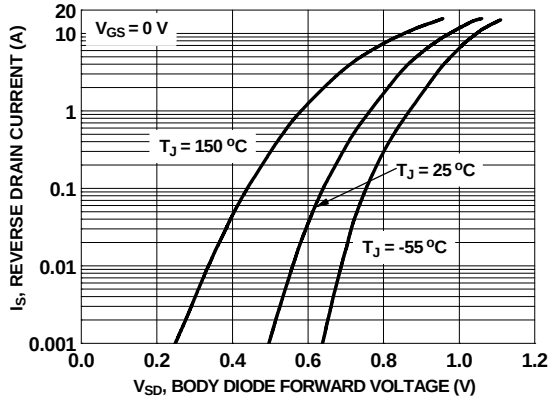


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25 °C unless otherwise noted

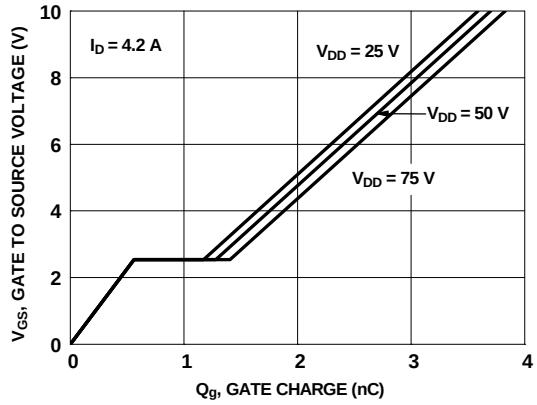


Figure 7. Gate Charge Characteristics

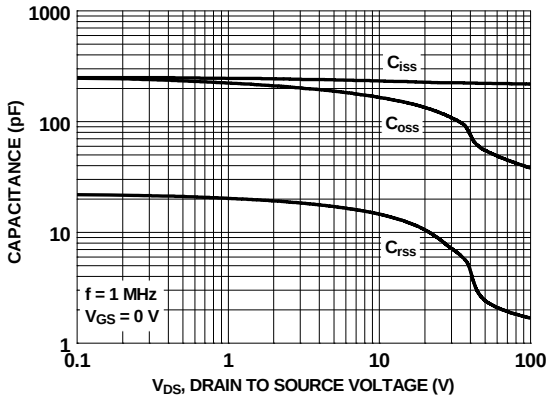


Figure 8. Capacitance vs Drain to Source Voltage

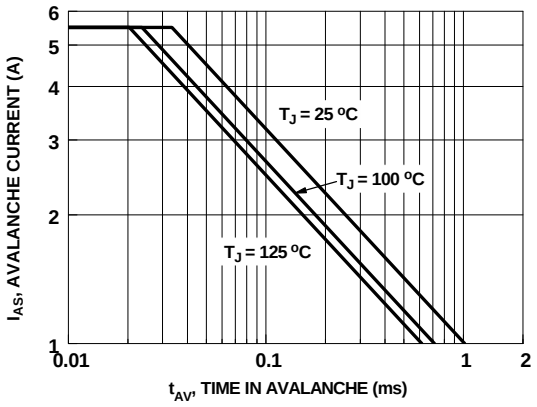


Figure 9. Unclamped Inductive Switching Capability

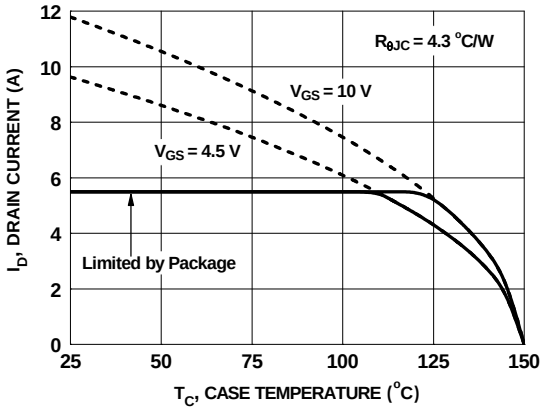


Figure 10. Maximum Continuous Drain Current vs Case Temperature

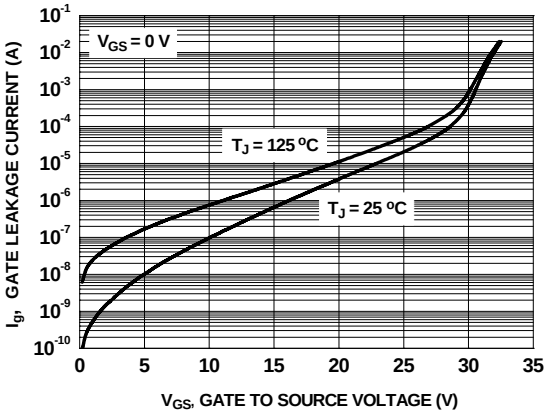


Figure 11. Gate Leakage Current vs Gate to Source Voltage

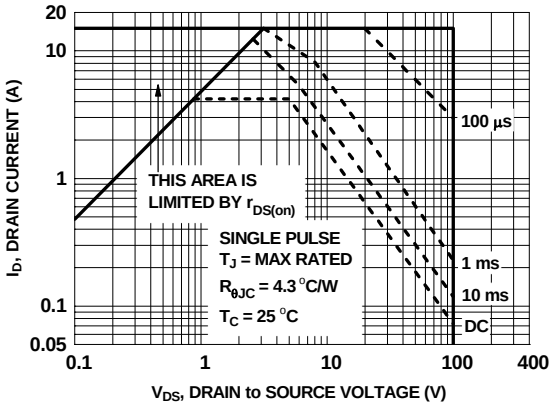


Figure 12. Forward Bias Safe Operating Area

Typical Characteristics T_J = 25 °C unless otherwise noted

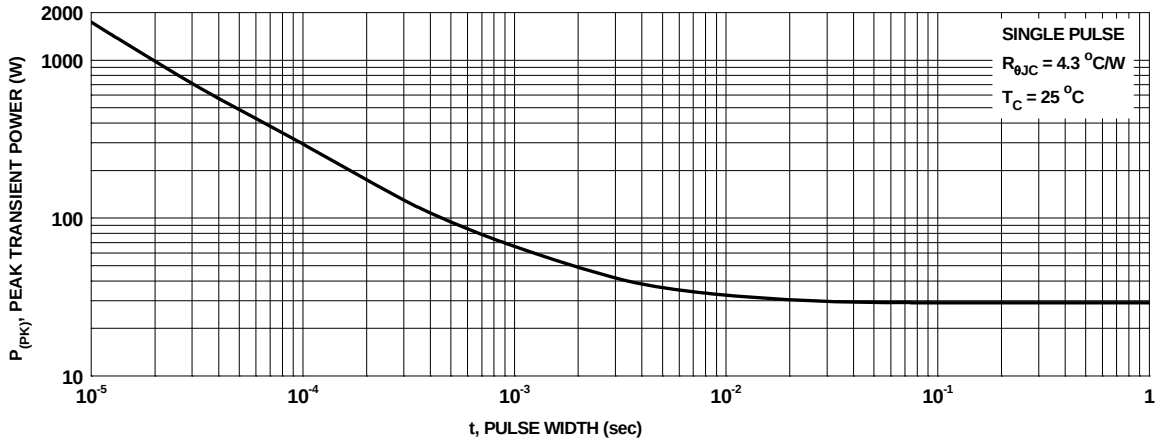


Figure 13. Single Pulse Maximum Power Dissipation

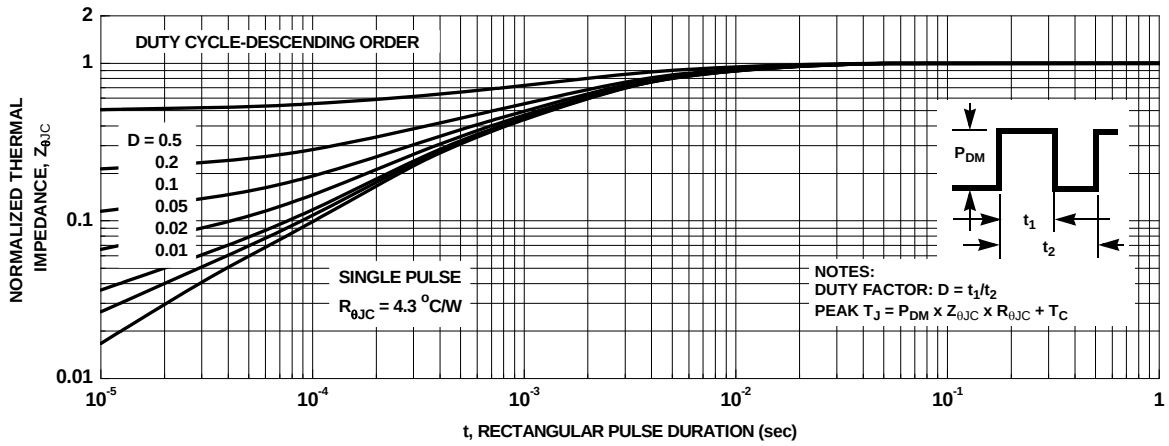
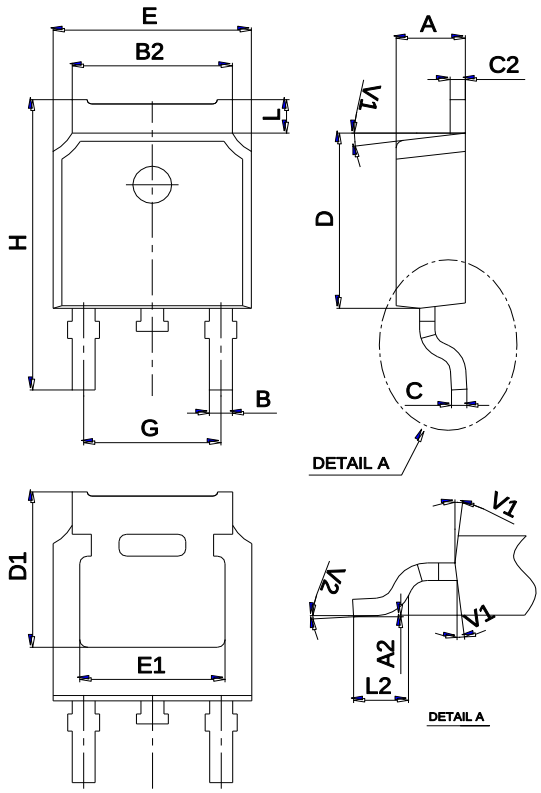


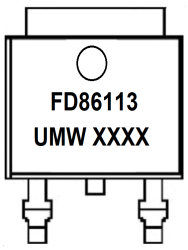
Figure 14. Junction-to-Case Transient Thermal Response Curve

Package Mechanical Data TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
UMW FDD86113LZ	TO-252	2500	Tape and reel

单击下面可查看定价，库存，交付和生命周期等信息

>>UMW(友台半导体)